

**• General Description**

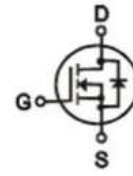
The ZM045N03N combines advanced trench MOSFET technology with a low resistance package to provide extremely low  $R_{DS(ON)}$ .

**• Features**

- Advance high cell density Trench technology
- Low  $R_{DS(ON)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

**• Application**

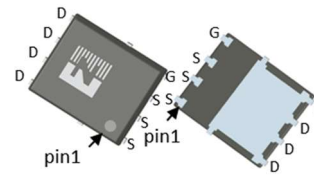
- MB/VGA Vcore
- SMPS 2<sup>nd</sup> Synchronous Rectifier
- POL application
- BLDC Motor driver

**• Product Summary**


$V_{DS} = 30V$

$R_{DS(ON)} = 4.5m\Omega$

$I_D = 75A$


**DFN5 x 6**
**• Ordering Information:**

Part NO.	ZM045N03N
Marking	ZM045N03
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

**• Absolute Maximum Ratings (T<sub>C</sub> = 25°C)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current	$I_{D@TC=25^{\circ}C}$	75	A
	$I_{D@TC=75^{\circ}C}$	57	A
	$I_{D@TC=100^{\circ}C}$	47	A
Pulsed Drain Current <sup>①</sup>	$I_{DM}$	180	A
Total Power Dissipation(TC=25°C)	$P_D@TC=25^{\circ}C$	80	W
Total Power Dissipation(TA=25°C)	$P_D@TA=25^{\circ}C$	2.5	W
Operating Junction Temperature	$T_J$	-55 to 150	°C
Storage Temperature	$T_{STG}$	-55 to 150	°C
Single Pulse Avalanche Energy	$E_{AS}$	200	mJ

**•Thermal resistance**

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.6	$^{\circ}C/W$
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	50	$^{\circ}C/W$
Soldering temperature, wavesoldering for 10s	$T_{sold}$	-	-	265	$^{\circ}C$

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu A$	1.2		2.5	V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$			1.0	$\mu A$
Gate- Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 20A$		4.5	6.0	$m\Omega$
		$V_{GS} = 4.5V, I_D = 10A$		7.0	9.0	$m\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 25V, I_D = 10A$		16		S
Source-drain voltage	$V_{SD}$	$I_S = 20A$		0.8	1.28	V

**•Electronic Characteristics**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 25V$ $f = 1MHz$	-	1500	-	pF
Output capacitance	$C_{oss}$		-	280	-	
Reverse transfer capacitance	$C_{rss}$		-	140	-	

**•Gate Charge characteristics( $T_a = 25^{\circ}C$ )**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Total gate charge	$Q_g$	$V_{DD} = 25V$	-	16	-	nC
Gate - Source charge	$Q_{gs}$	$I_D = 8A$	-	5	-	
Gate - Drain charge	$Q_{gd}$	$V_{GS} = 10V$	-	8	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS} = 10V, V_{DS} = 15V$ $R_G = 3.3\Omega, I_D = 15A$		7.5		ns
Turn-ON Rise time	$t_r$			14		ns
Turn-Off Delay time	$t_{D(off)}$			35		ns

Turn-Off Fall time	$t_f$		10	ns
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Note: ① Pulse Test : Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$  ;

Fig.1 Power Dissipation

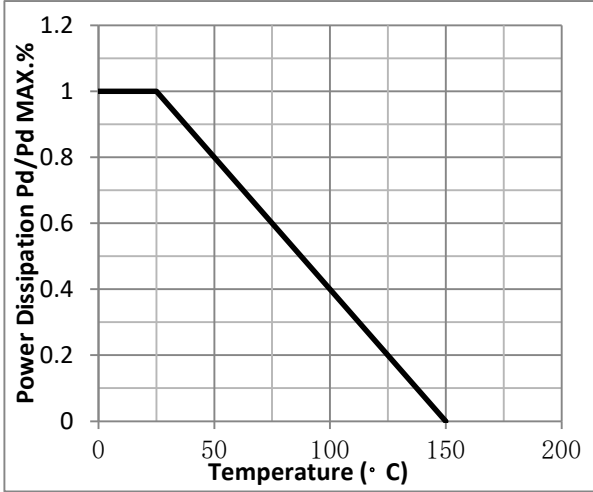


Fig.2 Typical output Characteristics

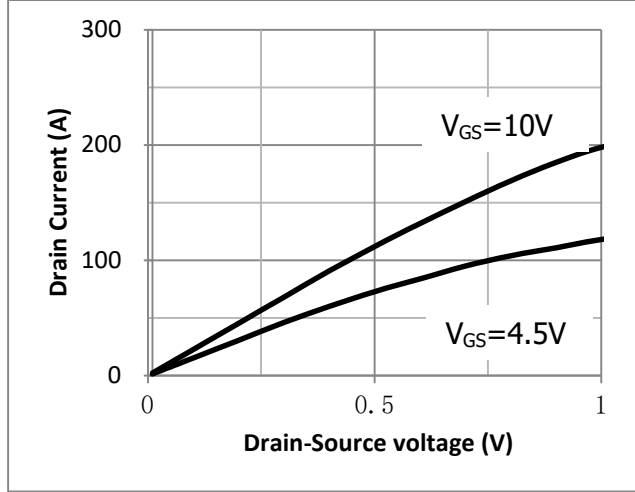


Fig.3 Threshold Voltage V.S Junction Temperature

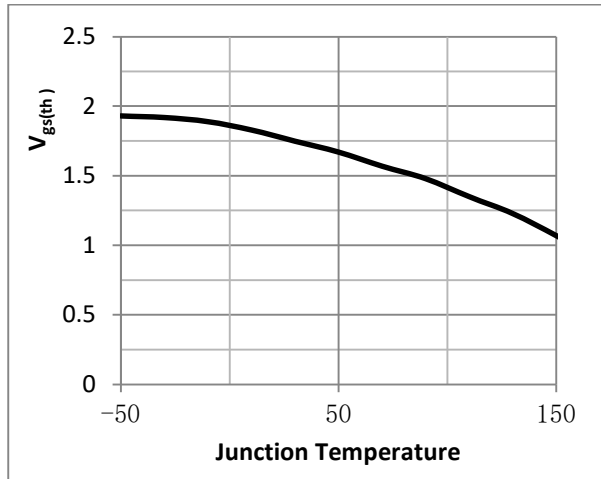


Fig.4 Resistance V.S Drain Current

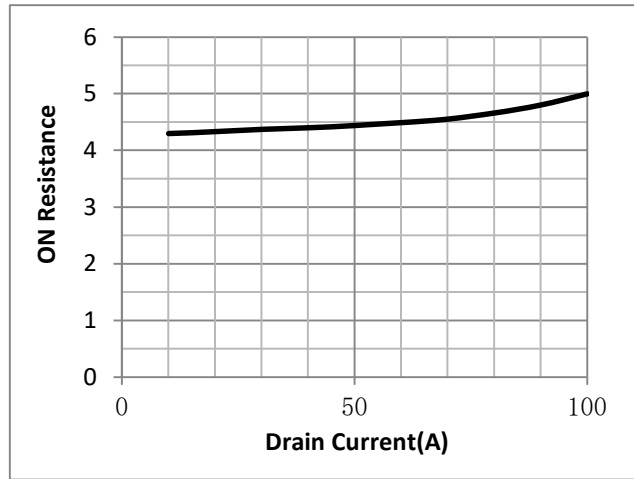


Fig.5 On-Resistance VS Gate Source Voltage

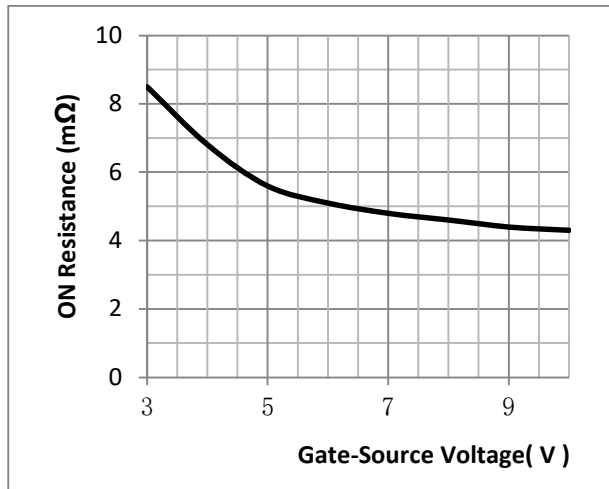


Fig.6 On-Resistance V.S Junction Temperature

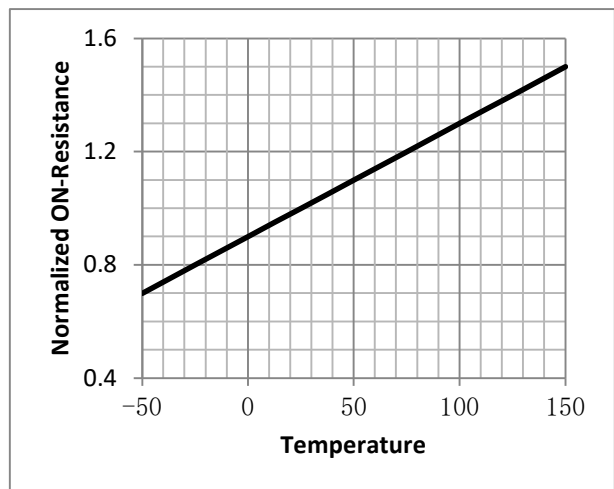


Fig.7 Gate Charge Measurement Circuit

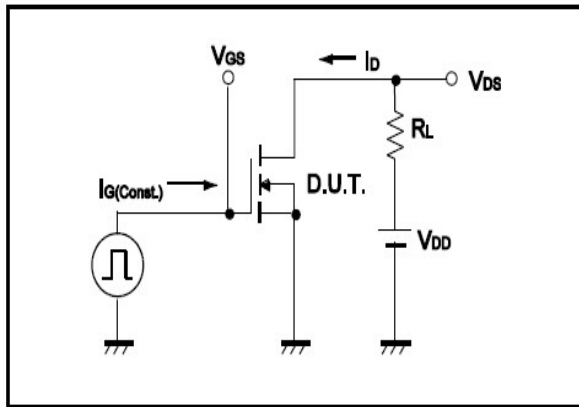


Fig.8 Gate Charge Waveform

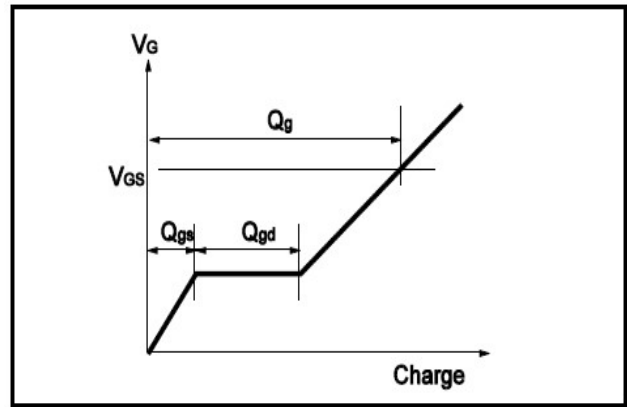


Fig.9 Switching Time Measurement Circuit

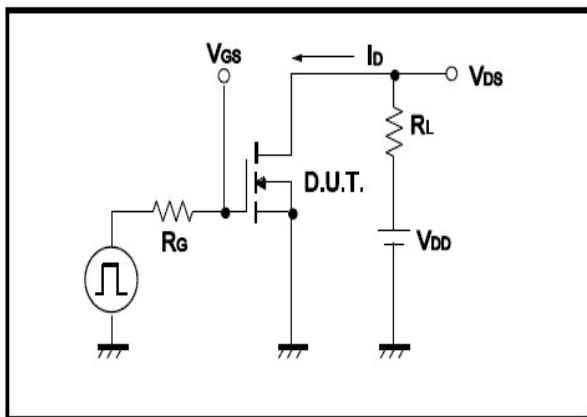


Fig.10 Switching Time Waveform

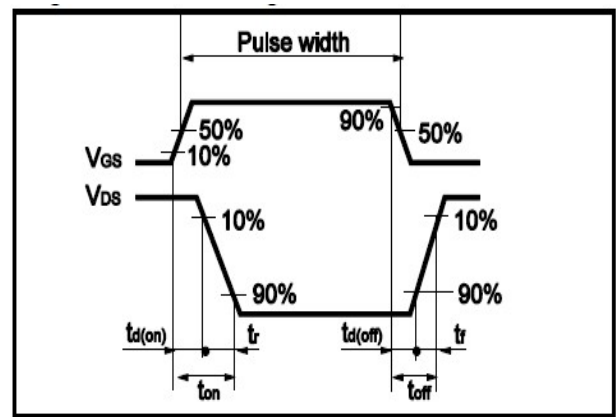


Fig.11 Avalanche Measurement Circuit

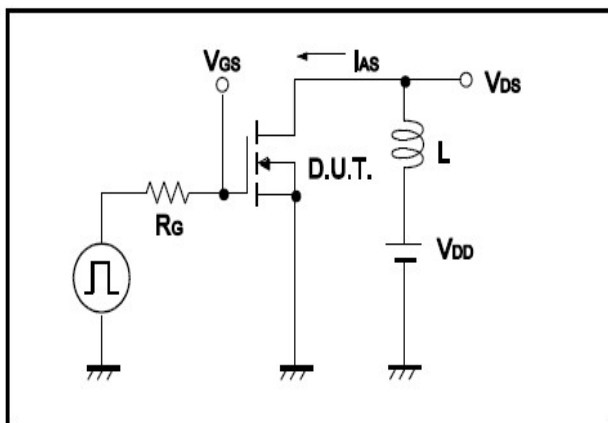


Fig.12 Avalanche Waveform

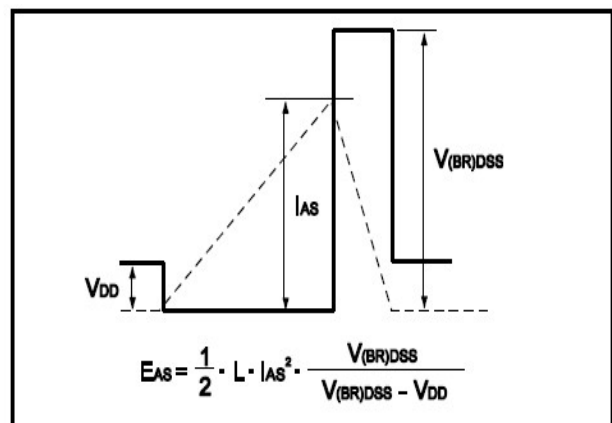
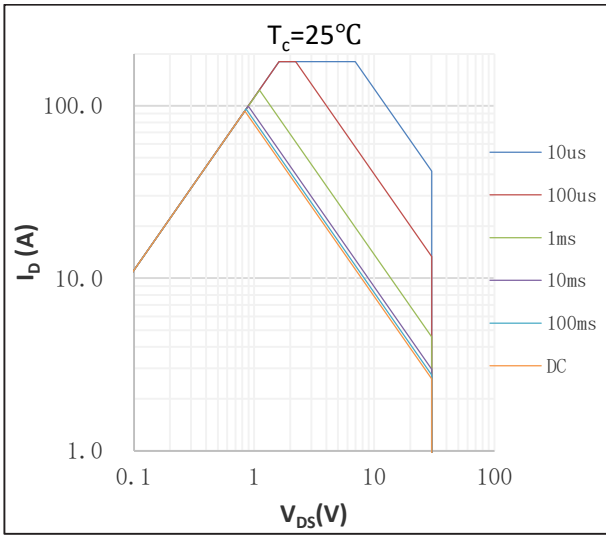




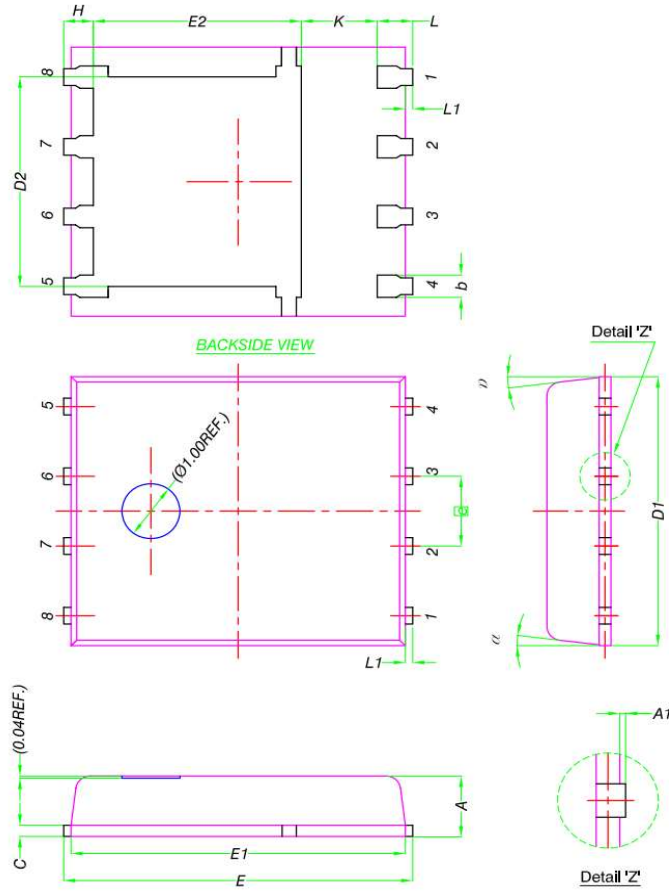
Fig.13 SOA





•Dimensions (DFN5×6)

Unit: mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.38	3.58	3.78
e	1.27 BSC		
H	0.41	0.51	0.61
K	1.10	-	-
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
α	0°	-	12°